

# 2N6035/2N6036 2N6038/2N6039

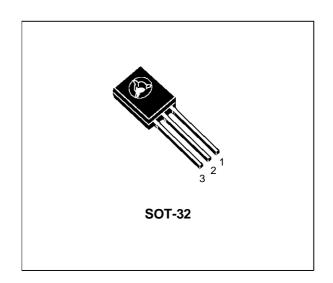
# COMPLEMENTARY SILICON POWER DARLINGTON TRANSISTORS

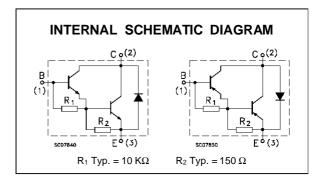
 2N6036 AND 2N6039 ARE SGS-THOMSON PREFERRED SALESTYPES

#### **DESCRIPTION**

The 2N6038 and 2N6039 are silicon epitaxial-base NPN power transistors in monolithic Darlington configuration mounted in Jedec SOT-32 plastic package.

The complementary PNP types are 2N6035 and 2N6036 respectively.





#### **ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter	Value			Unit
		PNP	2N6035	2N6036	
		NPN	2N6038	2N6039	
V <sub>CBO</sub>	Collector-Base Voltage (I <sub>E</sub> = 0)		60	80	V
V <sub>CEO</sub>	Collector-Emitter Voltage (I <sub>B</sub> = 0)		60	80	V
V <sub>EBO</sub>	Emitter-Base Voltage (I <sub>C</sub> = 0)		5		V
Ic	Collector Current		4		А
Ісм	Collector Peak Current		8		А
Ι <sub>Β</sub>	Base Current		0.1		А
Ptot	Total Dissipation at T <sub>c</sub> ≤ 25 °C		40		W
T <sub>stg</sub>	Storage Temperature		-65 to 150		°C
Tj	Max. Operating Junction Temperature		150		°C

For PNP types voltage and current values are negative.

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#### THERMAL DATA

Ī	R <sub>thj-case</sub>	Thermal Resistance Jur	nction-case Max	3.12	°C/W
	$R_{thj-amb}$	Thermal Resistance Jur	nction-ambient Max	83.3	°C/W

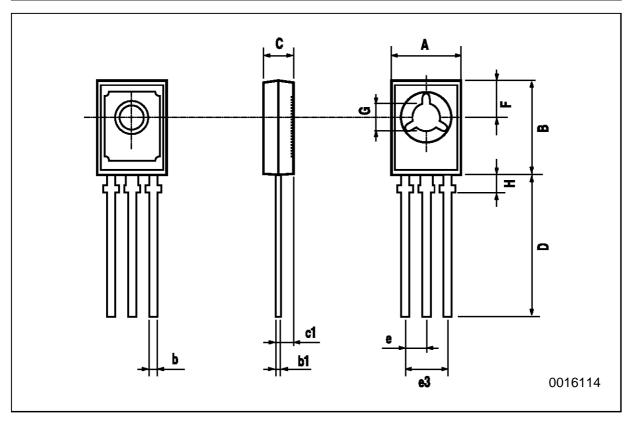
## **ELECTRICAL CHARACTERISTICS** (T<sub>case</sub> = 25 °C unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
I <sub>CEX</sub>	Collector Cut-off Current (V <sub>BE</sub> = -1.5V)	$V_{CE}$ = rated $V_{CEO}$ $V_{CE}$ = rated $V_{CEO}$ $T_c$ = 125 $^{\circ}$ C			0.1 0.5	mA mA
I <sub>CBO</sub>	Collector Cut-off Current (I <sub>E</sub> = 0)	V <sub>CE</sub> = rated V <sub>CBO</sub>			0.1	mΑ
I <sub>CEO</sub>	Collector Cut-off Current (I <sub>B</sub> = 0)	$V_{CE}$ = rated $V_{CEO}$			0.1	mΑ
I <sub>EBO</sub>	Emitter Cut-off Current (I <sub>C</sub> = 0)	V <sub>EB</sub> = 5 V			2	mA
V <sub>CEO(sus)*</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 100 mA for <b>2N6035/2N6038</b> for <b>2N6036/2N6039</b>	60 80			<b>&gt; &gt;</b>
V <sub>CE(sat)</sub> *	Collector-Emitter Saturation Voltage	$I_{C} = 2 A$ $I_{B} = 8 mA$ $I_{C} = 4 A$ $I_{B} = 40 mA$			2 3	> >
V <sub>BE(sat)*</sub>	Base-Emitter Saturation Voltage	$I_C = 4 \text{ A}$ $I_B = 40 \text{ mA}$			4	V
V <sub>BE</sub> *	Base-Emitter Voltage	$I_C = 2 A$ $V_{CE} = 3 V$			2.8	V
h <sub>FE</sub> *	DC Current Gain	Ic = 0.5 A	500 750 100		15000	
h <sub>fe</sub>	Small Signal Current Gain	I <sub>C</sub> = 0.75 A V <sub>CE</sub> = 10 V f = 1KHz	25			
Ссво	Collector Base Capacitance	$I_E = 0$ $V_{CB} = 10$ $V$ $f = 1MHz$ for <b>NPN types</b> for <b>PNP types</b>			100 200	pF pF

<sup>\*</sup> Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %

## **SOT-32 MECHANICAL DATA**

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
Α	7.4		7.8	0.291		0.307
В	10.5		10.8	0.413		0.445
b	0.7		0.9	0.028		0.035
b1	0.49		0.75	0.019		0.030
С	2.4		2.7	0.04		0.106
c1		1.2			0.047	
D		15.7			0.618	
е		2.2			0.087	
e3		4.4			0.173	
F		3.8			0.150	
G	3		3.2	0.118		0.126
Н			2.54			0.100



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